



Features and Benefits

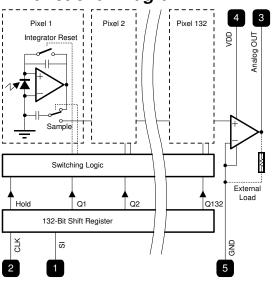
- 128 x 1 Sensor-Element Organization (1 Not Connected, 1 dummy, 128 real, 1 dummy and 1 Dark Pixel)
- 385 Dots-Per-Inch (DPI) Sensor Pitch
- High Linearity and Uniformity for 256 Gray-Scale (8-Bit) Applications
- High Sensitivity: 2.0V @ 10μW/cm² @ 0.7ms integration time for open cavity devices 1.7V @ 10μW/cm² @ 0.7ms integration time for glass lid devices
- Special Gain Compensation for use with single LED light source
- Output Referenced to Ground
- Low Image Lag
- Single 5V Supply
- Replacement for TAOS, Inc. TSL1301 & TSL1401 and MLX90255BA
- Operation to 800kHz

Applications

- Linear Position Encoder
- Rotary Position Encoder
- Steering Torque and Angle Sensing (EPAS, ESP)
- Spectrometer Applications
- Bio-metrical Applications
- OCR and Barcode Applications

Ordering Information

Part No.	Temperature Suffix	Package Code	Option code
MLX90255	K (-40 ℃ to 125 ℃)	XA (SOIC-24 without glass)	-BCR
MLX90255	K (-40 ℃ to 125 ℃)	UC (Die on wafer (un-sawn))	-BCV



1. Functional Diagram

2. Description

The MLX90255BC linear sensor array consists of a 128 x 1 array of photodiodes, associated charge amplifier circuitry and a pixel data-hold function that provides simultaneous-integration start and stop times for all pixels. The pixels measure 200 μ m (H) by 66 μ m (W). Operation is simplified by internal control logic that requires only a serial-input (SI) signal and a clock.

The sensor consists of 128 photodiodes arranged in a linear array. Light energy falling on a photodiode generates photocurrent, which is integrated by the active integration circuitry associated with that pixel. During the integration period, a sampling capacitor connects to the output of the integrator through an analog switch. The amount of charge accumulated at each pixel is directly proportional to the light intensity and the integrators is controlled by a 132-bit shift register and reset logic. An output cycle is initiated by clocking in a logic 1 on SI. *(continued on page 5)*





Linear Optical Array

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3. MLX90255BC Electrical Specifications

DC Operating Parameters $T_A = -40^{\circ}$ C to 125° C, $V_{DD} = 4.5$ V to 5.5V (unless otherwise specified)ParameterSymbolTest ConditionsMinTypMaxUnits

	•				
Supply voltage	Vdd	4.5	5	5.5	V
Input voltage	Vi	0		Vdd	V
High-level input voltage	Vih	Vdd*0.7		Vdd	V
Low-level input voltage	Vil	0		Vdd*0.3	V
Hysteresis on SI and CLK		0.2	0.4	0.8	V
Wavelength of light source		400		1000	nm
Clock frequency	Fclock	64		800	kHz
Sensor integration time below 60°C (1)	Tint	0.125		100	ms
Sensor integration time (full temperature range) (2)	Tint	0.125		2	ms
Pixel charge transfer time (full temp range)	Tqt	8			μs
Setup time, serial input	Tsu(SI)	350			ns
Hold time, serial input (3)	Th(SI)	160			ns
Operating free-air temperature	Та	-40		125	°C
Clock pulse duration (high)	Tw(H)	625			ns
Clock pulse duration (low)	Tw(L)	625			ns

Notes:

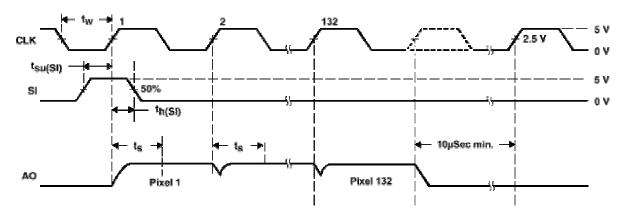
(1) Reset until clock pulse 18 (on declining flank).

Minimum integration time = (133-18) * CLK period + 10µs (this is the time the S&H cap needs to follow).

At 1MHz clock speed, the minimum integration time becomes 0.125ms.

(2) At $125 \,^{\circ}$ C, the integration time should be limited to 2ms.

(3) The SI pulse must go low before the rising edge of the next clock pulse.





MLX90255BC Electrical specifications

All tests are made with 0.7ms integration time at 25 °C at 880nm and with a clock speed of 500kHz in, 250kHz out, and 500kHz, unless otherwise specified in the Test Conditions. 100% light under Test Conditions means that the light is set in such a way that there is 2.4V at the output of the chip.

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units	
Sensitivity for devices with glas lid	Sensitivity	At 25°C	0.135	0.151	0.179	V/µW/	
Sensitvity for open devices			0.14	0.16	0.19	cm2	
Polyimide Wafer			0.14	0.176	0.21		
Illumination (1)	Illum100	At 25°C, 2.4V at output		14		µW/cm²	
Average analog output (1)	VaoLight	At 25°C, 100% light		2.4		V	
Average analog output	Initial offset	At 25°C, 0% light	0	0.15	0.3	V	
Average analog output	VaoDark	At 125°C, 0% light	0	0.40	1.4	V	
Highest Dark Pixel	Vaodarkmax	At 125°C, 0.25ms integration time			0.8	V	
Non Linearity	Nlao1	All Temp		±0.5%	±1.2%	FS	
Pixel Response Non Uniformity (2)	PRNU	All Temp, 100% light		±4.0%	±8.5%	FS	
Pixel Interaction Test (3)	PIT	AT 25°C		5%		FS	
Noise Level (4)	Vn	All Temp		3	6	mV (RMS)	
Hold spec, same as PRNU	PRNUH	All Temp, 100% light, 62.5kHz		±4.0%	±8.5%	FS	
Output Settling Time	Ts	All Temp		450	750	ns	
Array Lag (5)	Alag	At 25°C		0.5%		FS	
Dark Signal Non Uniformity (6)	DSNU	At 25°C		80	120	mV	
		At 125°C		140	440	mV	
Analog Output Saturation		All Temp	3.0			V	
Change in sensitivity with Temperature at 880nm (7)				0.3		%/°C	
Operating Free Temp			-40		125	°C	
Supply Current (8)	ldd		2	5	8	mA	

(0) After power on, the first integration scan is not guaranteed correct. This scan is needed for initializing digital levels on chip. After a SI and 133 proper CLK signals, the system is fully initialized and all further scans are valid. The next SI will provide a valid scan.

(1) Absolute Light measurements are very test-setup dependent and should be regarded with caution. Relative measurements are possible with ±1% accuracy.

(2) PRNU is defined as the worst case deviation of any PixelValue (pixel 3 till 130) to the average light value. PixelValue = (Vout of a pixel at 100% light – Vout of same pixel at 0% light) The MLX90255BC has a cosine shaped gain: external pixels have 15% more gain than middle pixels.

(3) PIT = (Vout of pixel 132 @ 10μ W – Vout of pixel 132 @ 0μ W) / (Vaverage @ 10μ W – Vaverage @ 10μ W)

(4) Noise: We compare 5 different measurements, normalize them and then take the RMS value.

(5) Array Lag is defined as: (Vaverage 0μW1 Vaverage 0μW2) / ((Vaverage 10μW Vaverage 0μW2). Where 0μW1 is a 0% light level, 1ms after a 100% light level. (there can still be some light effects). 0μW2 is a 0% light level, 10ms after a 100% light level, which should be a true dark reference.

(6) DSNU is defined as: (max Vout of pixel I @ 0% light) - (min Vout of pixel j @ 0% light) for pixels 3 thru 130

(7) Sensitivity always increases with rising temperature.

(8) Idd is measured with Rload disconnected from the output pin.



4. General Description

(continued from page 1)

This causes all 132 sampling capacitors to be disconnected from their respective integrators and starts an integrator reset period. As the SI pulse is clocked through the shift register, the charge stored on the sampling capacitors is sequentially connected to a charge-coupled output amplifier that generates a voltage on the analog output AO. Two dummy pixel values are shifted out first, then the 128 actual pixel bits, followed by two additional dummy pixel bits, for a total of 132 data bits. Although there are only 132 pixels, 133 clock pulses are necessary for a complete shift out. The final pulse is used to reinitialize the shift register.

The integrator reset period ends 18 clock cycles after the SI pulse is clocked in. So the lightintegration starts after the 18th CLK pulse. The light-integration ends at the next SI pulse. Between the end of the 133th clock pulse and the next SI pulse, a minimum time of 10µs is necessary for an effective S&H function. So the minimum integration time of the MLX90255BC is (133 -18) * Ts + 10µs and thus dependent on clock speed. (Ts = clock period) After the 132data bits are clocked out, the output becomes high impedance. (see figure) The AO is driven by a source follower that requires an external pulldown resistor. (typically 330Ω) The output is nominally 125mV for no light input and 2.4V for a nominal full-scale output. The pixel gain is 15% bigger at the edges than in the middle (cosine correction) in order to get a flat output when illuminating the device with a single LED light source (see also Section 6).

The MLX90255BC is intended for use in a wide variety of applications, including: image scanning, mark and code reading, optical character recognition (OCR) and contact imaging, edge detection and positioning, and optical linear and rotary encoding. The MLX90255BC is a replacement for the Texas Instruments' TSL1301 and TSL1401 parts.

5. Absolute Maximum Ratings

Supply Voltage, Vdd	+7V
Digital Input Current Range	-20 to 20 mA
Operating Free-Air temperature range, Ta	-40°C to 125°C (automotive compliant optical package)
Storage temperature range, Tstg	-40°C to 125°C
ESD Sensitivity (Human Body Model according to CDF-AEC- Q100-002)	2kV

Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device.

These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied.

Exposure to absolute-maximum -rated conditions for extended periods may affect device reliability.



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6. Cosine Correction

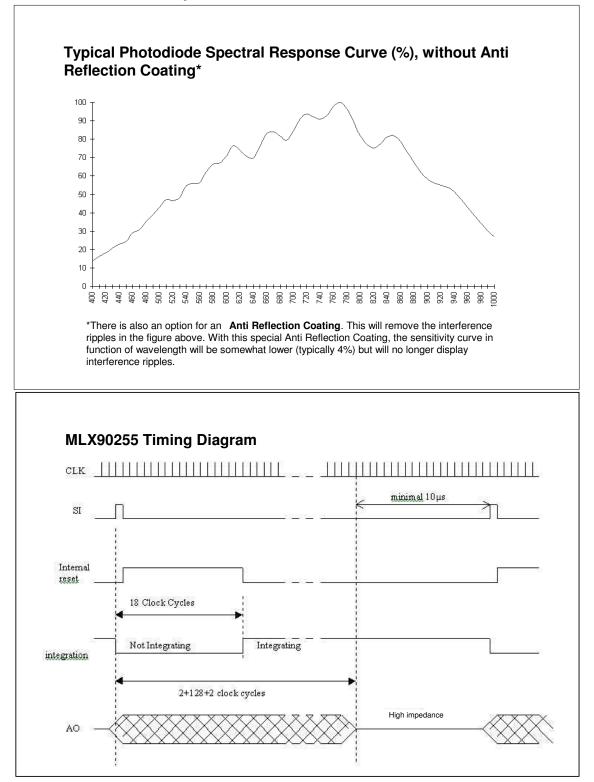
When using a single LED light source, which is placed above the middle of the die, the light intensity that falls onto the outer pixels is lower than the light intensity that falls onto the middle pixels (due to the distance die-LED, the shape of the LED light emission and the sensitivity of pixels vs. angle of incident light). To compensate for these effects, each pixel in the array has a slightly different gain correction with respect to the centre of the array. For a light source to photodiode array distance of 15mm the relative pixels sensitivities are shown in the table below.

Pixe num	el 1ber	Relative Pixel Sensitivity		Pixel number		Relative Pixel Sensitivity	Pixel number			Relative Pixel Sensitivity	Pixel number		Relative Pixel Sensitivity
1	132	1.1703	1	8	115	1.0912		35	98	1.0376	52	81	1.0076
2	131	1.1649	1	9	114	1.0874		36	97	1.0352	53	80	1.0066
3	130	1.1596	2	0	113	1.0836		37	96	1.0328	54	79	1.0056
4	129	1.1544	2	1	112	1.0799		38	95	1.0306	55	78	1.0047
5	128	1.1493	2	2	111	1.0764		39	94	1.0284	56	77	1.0039
6	127	1.1442	2	3	110	1.0729		40	93	1.0263	57	76	1.0031
7	126	1.1393	2	4	109	1.0695		41	92	1.0243	58	75	1.0025
8	125	1.1345	2	5	108	1.0661		42	91	1.0224	59	74	1.0019
9	124	1.1298	2	6	107	1.0629		43	90	1.0206	60	73	1.0014
10	123	1.1251	2	7	106	1.0598		44	89	1.0188	61	72	1.0010
11	122	1.1206	2	8	105	1.0567		45	88	1.0171	62	71	1.0006
12	121	1.1161	2	9	104	1.0537		46	87	1.0155	63	70	1.0003
13	120	1.1117	3	0	103	1.0508		47	86	1.0140	64	69	1.0002
14	119	1.1074	3	1	102	1.0480		48	85	1.0126	65	68	1.0000
15	118	1.1032	3	2	101	1.0453		49	84	1.0112	66	67	1.0000
16	117	1.0991	3	3	100	1.0426		50	83	1.0099			
17	116	1.0951	3	4	99	1.0400		51	82	1.0087			



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7. Performance Graphs





8. Standard information regarding manufacturability of Melexis products with different soldering processes

Our products are classified and qualified regarding soldering technology, solderability and moisture sensitivity level according to following test methods:

Reflow Soldering SMD's (Surface Mount Devices)

- IPC/JEDEC J-STD-020 Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices (classification reflow profiles according to table 5-2)
- EIA/JEDEC JESD22-A113 Preconditioning of Nonhermetic Surface Mount Devices Prior to Reliability Testing (reflow profiles according to table 2)

Wave Soldering SMD's (Surface Mount Devices) and THD's (Through Hole Devices)

EN60749-20

Resistance of plastic- encapsulated SMD's to combined effect of moisture and soldering heat EIA/JEDEC JESD22-B106 and EN60749-15

Resistance to soldering temperature for through-hole mounted devices

Iron Soldering THD's (<u>Through Hole Devices</u>)

 EN60749-15 Resistance to soldering temperature for through-hole mounted devices

Solderability SMD's (Surface Mount Devices) and THD's (Through Hole Devices)

• EIA/JEDEC JESD22-B102 and EN60749-21 Solderability

For all soldering technologies deviating from above mentioned standard conditions (regarding peak temperature, temperature gradient, temperature profile etc) additional classification and qualification tests have to be agreed upon with Melexis.

The application of Wave Soldering for SMD's is allowed only after consulting Melexis regarding assurance of adhesive strength between device and board.

Melexis is contributing to global environmental conservation by promoting **lead free** solutions. For more information on qualifications of **RoHS** compliant products (RoHS = European directive on the Restriction Of the use of certain Hazardous Substances) please visit the quality page on our website: <u>http://www.melexis.com/quality.asp</u>

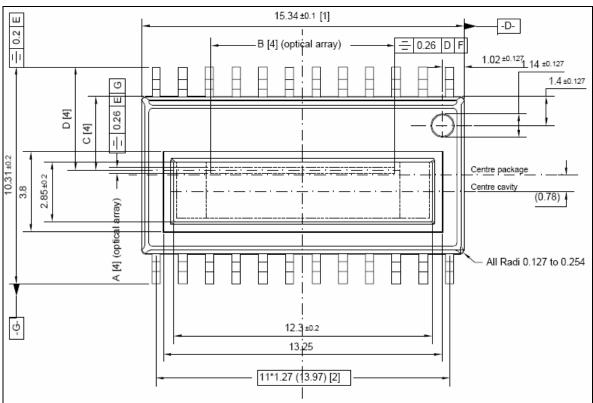
9. ESD Precautions

Electronic semiconductor products are sensitive to Electro Static Discharge (ESD). Always observe Electro Static Discharge control procedures whenever handling semiconductor products.



10. Package Information

10.1. MLX90255KXA-BCR (SOIC-24 without glass) package dimensions

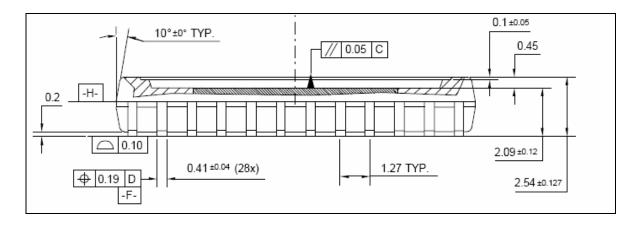


A = 200um pixel height

 $B = 132 \times 66$ um = 8712 um, mid 128 pixels are usefull pixels

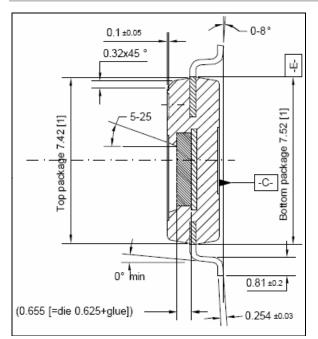
C = 3.53 + -0.13 (tolerance is indicated on the drawing as 0.26 in absolute deviation)

D = 4.92 + -0.13 (tolerance in again indicated on the drawing as 0.26 in absolute deviation)





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10.2. XA (SOIC-24 without glass) Pin Description

Pin	Sym bol	Description
5	SI	Serial Input. Si defines the start of the data-out sequence
6	CLK	Clock. CLK controls the charge transfer, pixel output and reset (together with SI)
7	A0	Analog Output
8	Vdd	Supply voltage, for both analog and digital circuits
3,4,9,10, 15,16,21,22	Vss	Ground (substrate). All Vss Pins are referenced to the substrate.



10.3. MLX90255KUC-BCV (Wafer Polyimide)

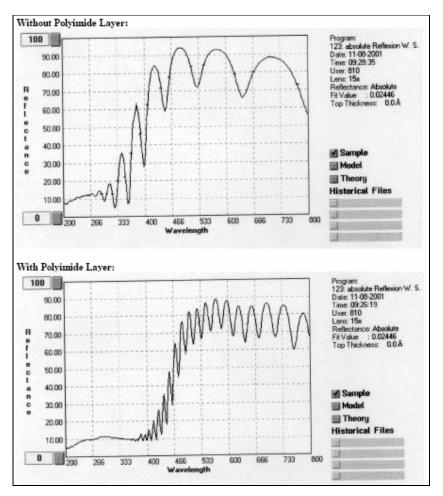
Die on wafer (unsawn) with polyimide passivation.

- Advantages: Extra adhesion by polyimide layer
- Disadvantages: The sensitivity of a wafer with polyimide layer is ~20% less than on a normal wafer without this layer

Light Transmission Properties of Polyimide Layer

Method of Measurement:

- Testwafer with AlSiCu + Passivation Layer
- Measure of absolute Reflectance with NANOSPEC about maximal wavelength area





MLX90255-BC

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11. Disclaimer

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